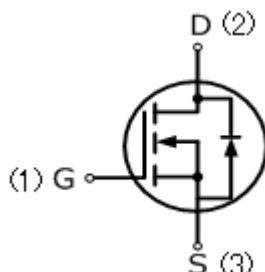


## 20N65Y

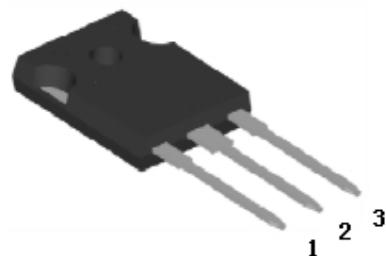
20 Amps, 650 Volts N-CHANNEL MOSFET

### FEATURE

- 20A, 650V,  $R_{DS(ON)MAX}=0.50\ \Omega$  @  $V_{GS}=10V/10A$
- Low gate charge
- Low  $C_{iss}$
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-247-3L



### Absolute Maximum Ratings ( $T_c=25^\circ C$ , unless otherwise noted)

Parameter	Symbol	20N65Y	UNIT
Drain-Source Voltage	$V_{DSS}$	650	V
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	
Continuous Drain Current	$I_D$	20	A
Pulsed Drain Current (Note 1)	$I_{DM}$	80	
Single Pulse Avalanche Energy (Note 2)	$E_{AS}$	980	mJ
Reverse Diode $dV/dt$ (Note 3)	$dV/dt$	5	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	$T_L$	260	°C

### Thermal Characteristics

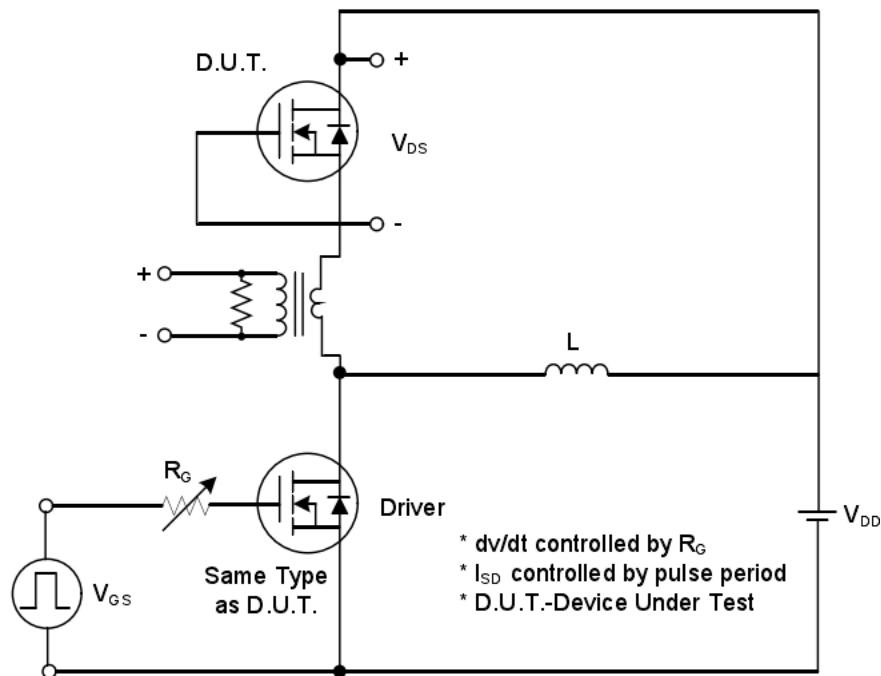
Parameter	Symbol	TO-247-3L	Units
Maximum Junction-to-Case	$R_{thJC}$	0.54	°C/W
Maximum Power Dissipation	$T_c=25^\circ C$	$P_D$	W

Electrical Characteristics ( $T_c=25^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	650	—	—	V
Breakdown Temperature Coefficient $/\Delta T_J$	$\Delta \text{BV}_{\text{DSS}}$	Reference to $25^\circ\text{C}$ , $I_{\text{D}}=250\mu\text{A}$	—	0.6	—	$\text{V}/^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}$	—	—	1	$\mu\text{A}$
Gate-Body Leakage Current, Forward	$I_{\text{GSSF}}$	$V_{\text{GS}}=30\text{V}, V_{\text{DS}}=0\text{V}$	—	—	100	nA
Gate-Body Leakage Current, Reverse	$I_{\text{GSSR}}$	$V_{\text{GS}}=-30\text{V}, V_{\text{DS}}=0\text{V}$	—	—	-100	nA
<b>On Characteristics</b>						
Gate-Source Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2	—	4	V
Drain-Source On-State Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=10\text{A}$	—	0.42	0.5	$\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V},$ $f=1.0\text{MHz}$	—	2983	—	pF
Output Capacitance	$C_{\text{oss}}$		—	316	—	pF
Reverse Transfer Capacitance	$C_{\text{rss}}$		—	20	—	pF
<b>Switching Characteristics</b>						
Turn-On Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=250\text{V}, I_{\text{D}}=20\text{A},$ $R_G=10\Omega$ (Note 3,4)	—	36	—	ns
Turn-On Rise Time	$t_r$		—	74.7	—	ns
Turn-Off Delay Time	$t_{\text{d(off)}}$		—	78.7	—	ns
Turn-Off Fall Time	$t_f$		—	58.7	—	ns
Total Gate Charge	$Q_g$	$V_{\text{DS}}=400\text{V}, I_{\text{D}}=20\text{A},$ $V_{\text{GS}}=10\text{V}$ , (Note 3,4)	—	58	—	nC
Gate-Source Charge	$Q_{\text{gs}}$		—	13.3	—	nC
Gate-Drain Charge	$Q_{\text{gd}}$		—	22.9	—	nC
<b>Drain-Source Body Diode Characteristics and Maximum Ratings</b>						
Continuous Diode Forward Current	$I_s$	$I_s=20\text{A}, V_{\text{GS}}=0\text{V}$	—	—	20	A
Pulsed Diode Forward Current	$I_{\text{SM}}$		—	—	80	A
Diode Forward Voltage	$V_{\text{SD}}$		—	—	1.5	V
Reverse Recovery Time	$t_{\text{rr}}$		—	584	—	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		—	6.85	—	$\mu\text{C}$

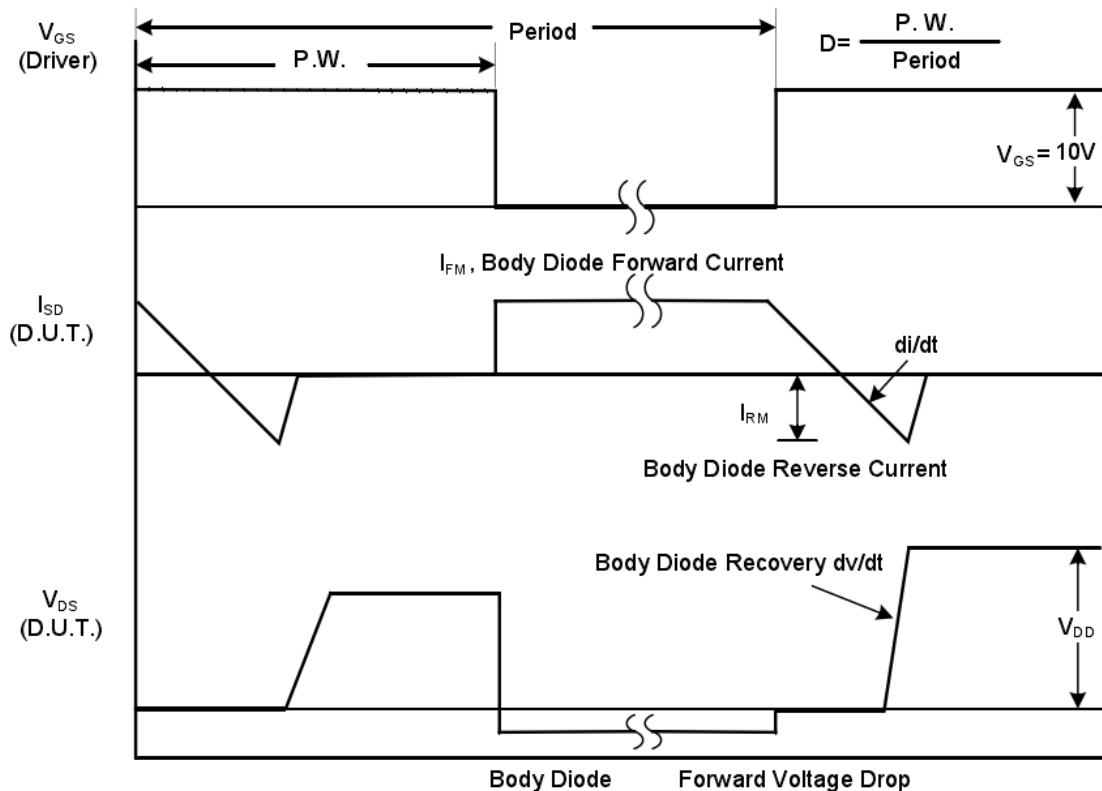
#### Notes

- Repetitive Rating; pulse width limited by maximum junction temperature.
- $V_{\text{DD}}=50\text{V}, L=10\text{mH}, R_g=25\Omega, I_{\text{AS}}=14\text{A}$ , starting  $T_J=25^\circ\text{C}$ .
- $I_{\text{SD}} \leq I_{\text{D}}, dI/dt=200\text{A/us}, V_{\text{DD}} \leq \text{BV}_{\text{DSS}}$ , starting  $T_J=25^\circ\text{C}$ , Pulse width  $\leq 300\text{us}$ ; duty cycle  $\leq 2\%$ .
- Repetitive rating; pulse width limited by maximum junction temperature.

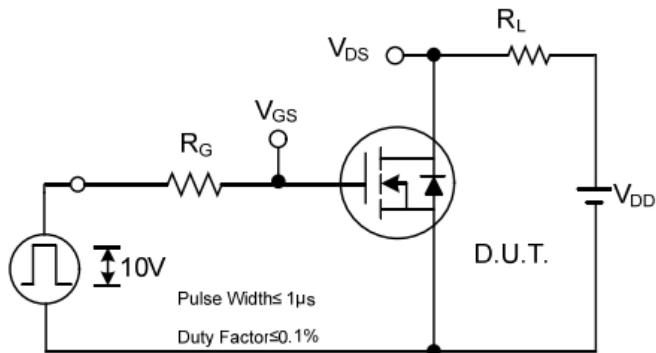
## RATING AND CHARACTERISTIC CURVES



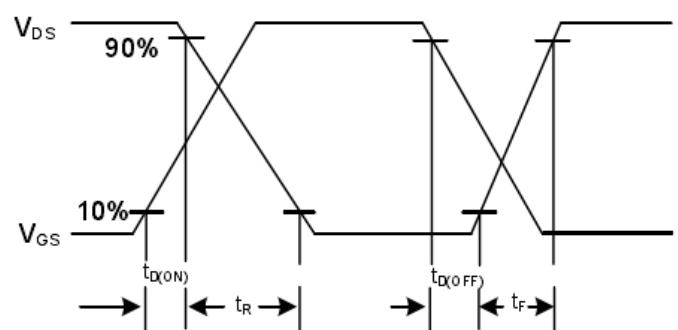
Peak Diode Recovery dv/dt Test Circuit



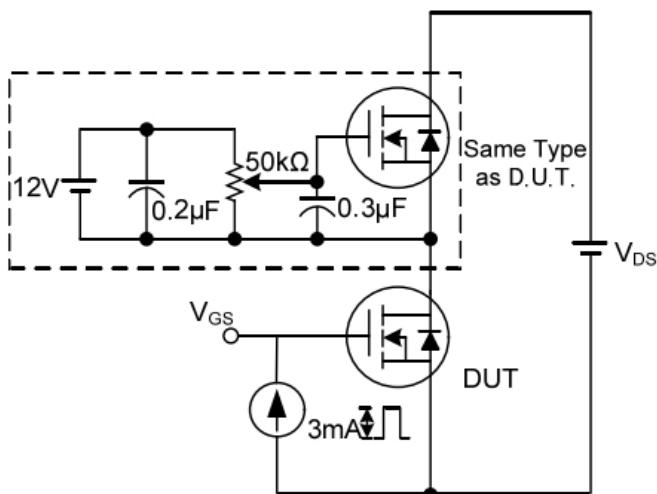
Peak Diode Recovery dv/dt Waveforms



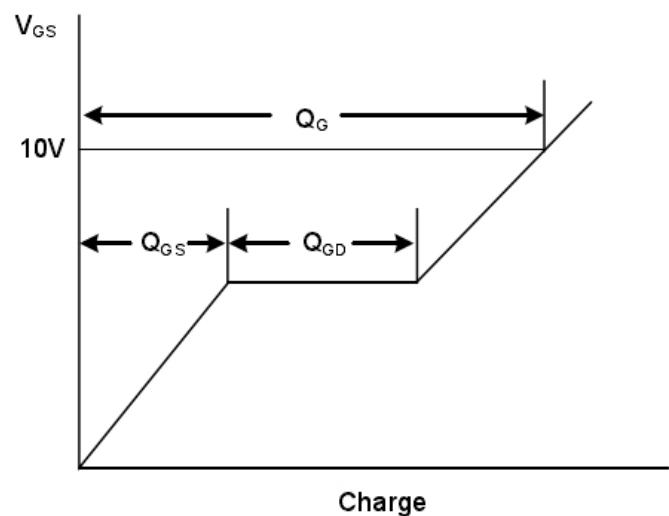
Switching Test Circuit



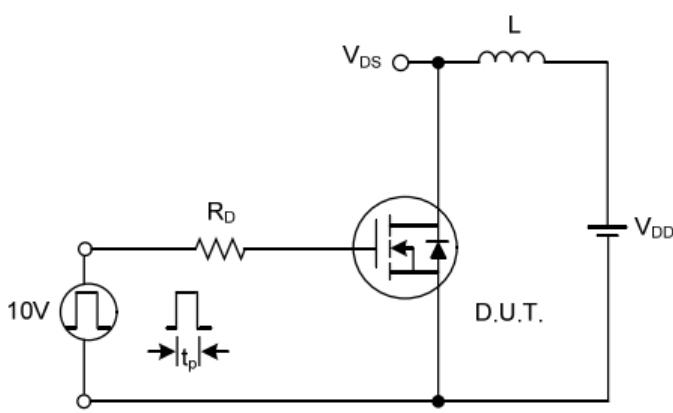
Switching Waveforms



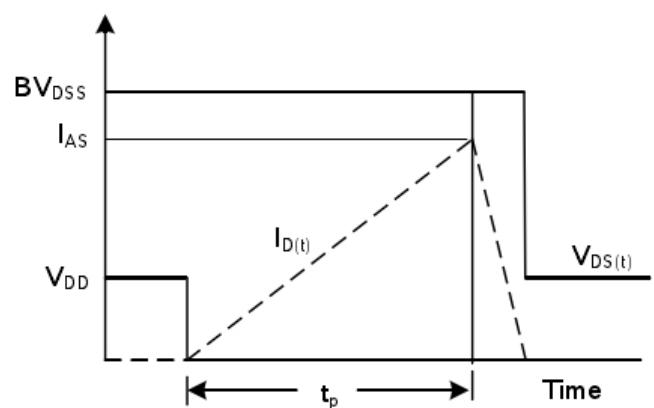
Gate Charge Test Circuit



Gate Charge Waveform

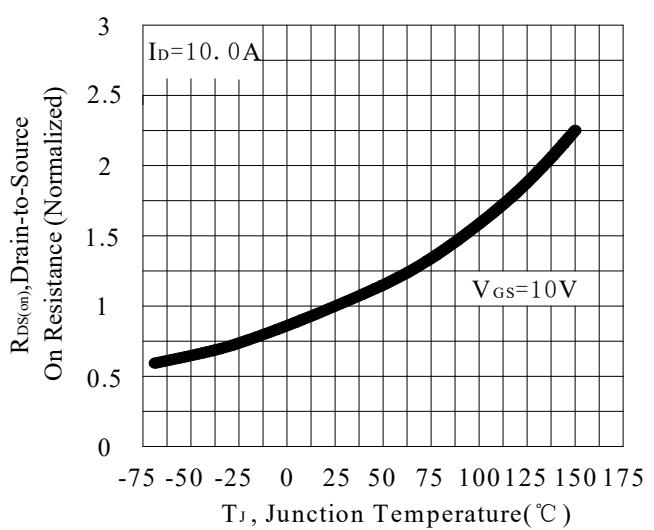
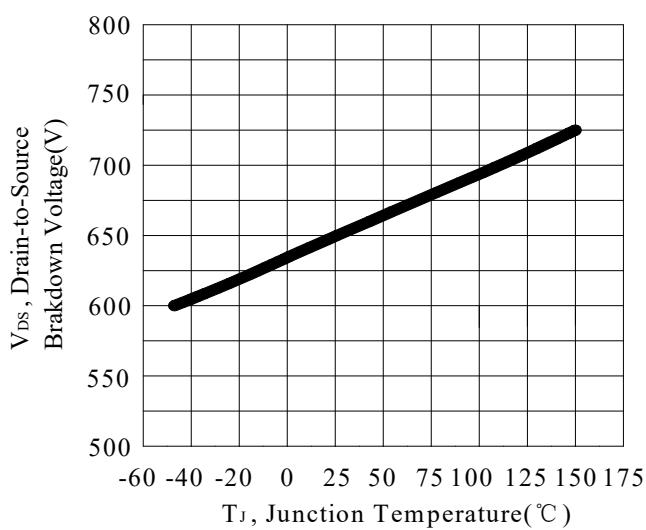
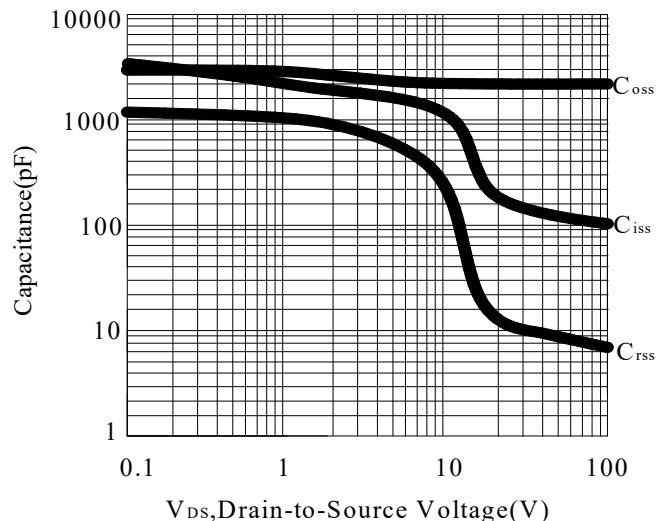
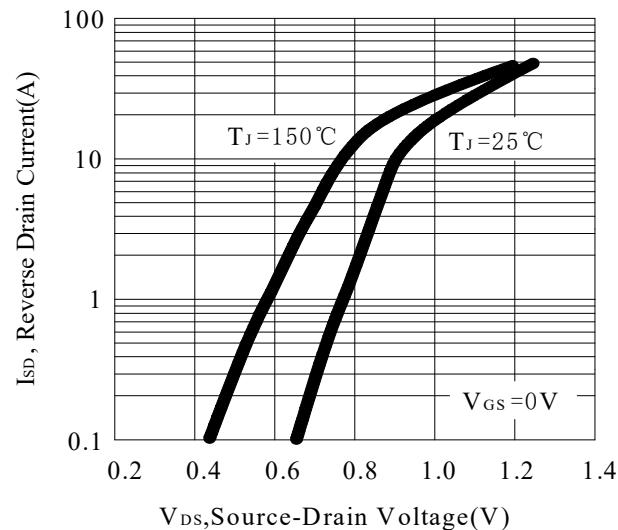
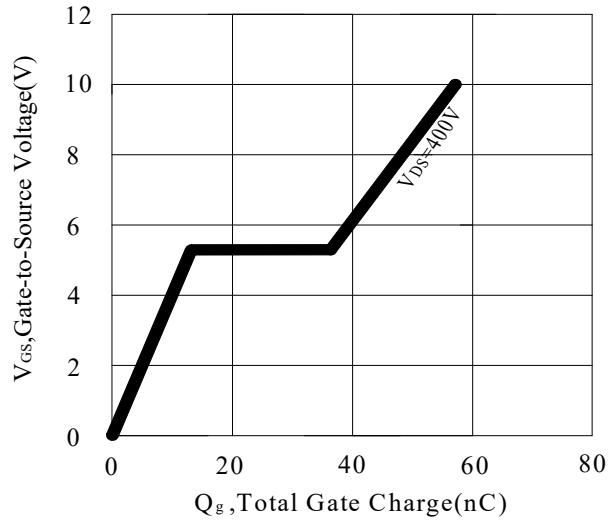
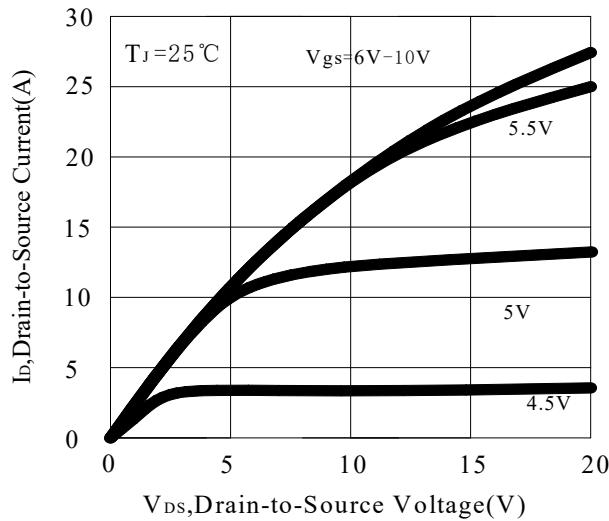


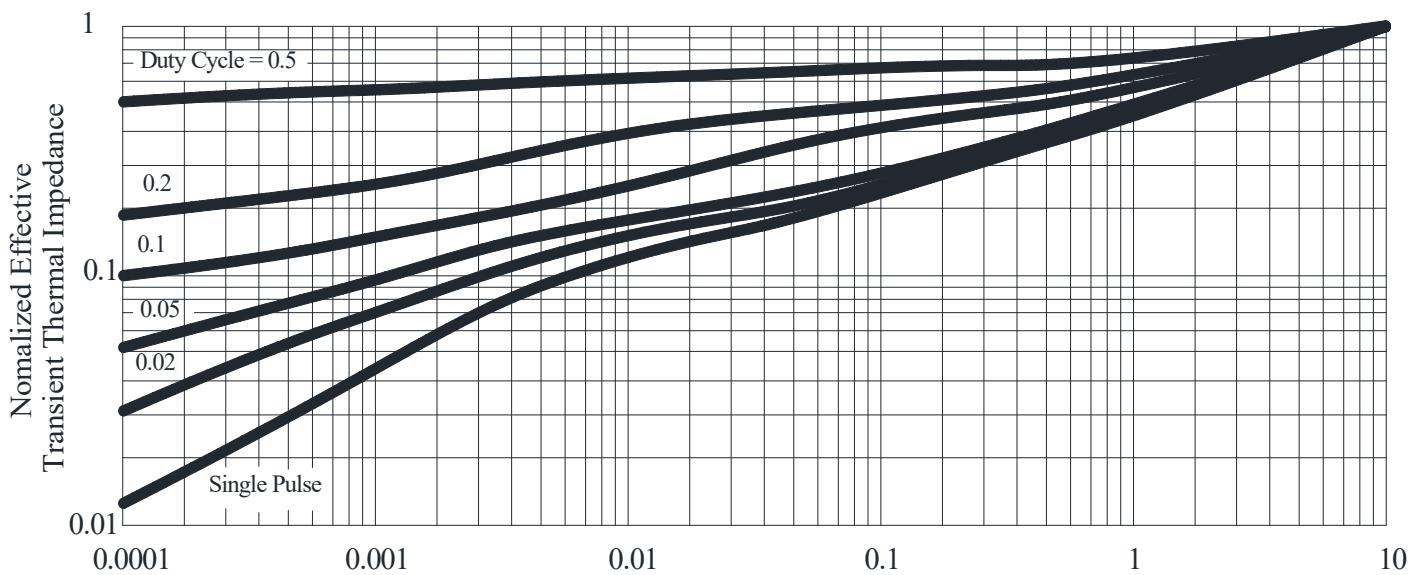
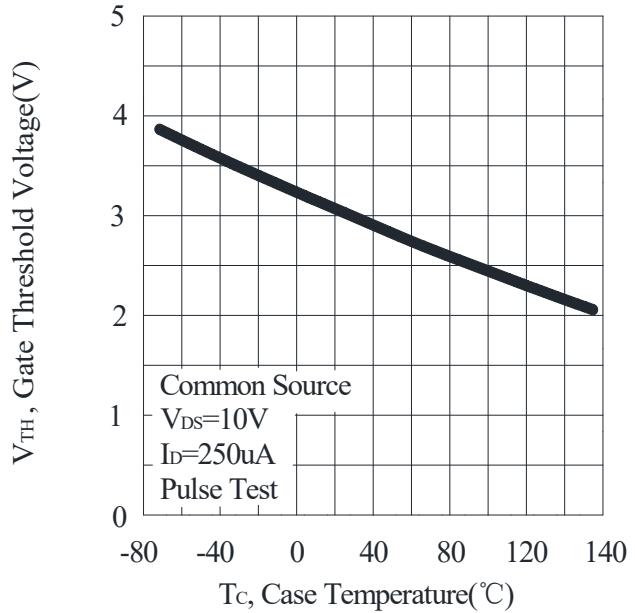
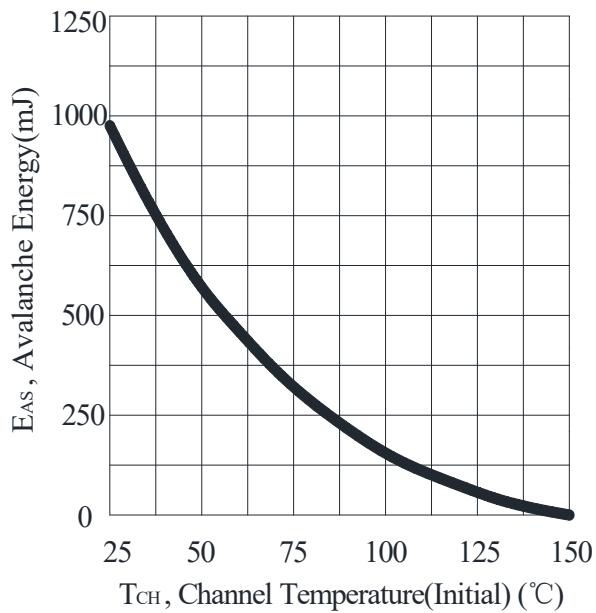
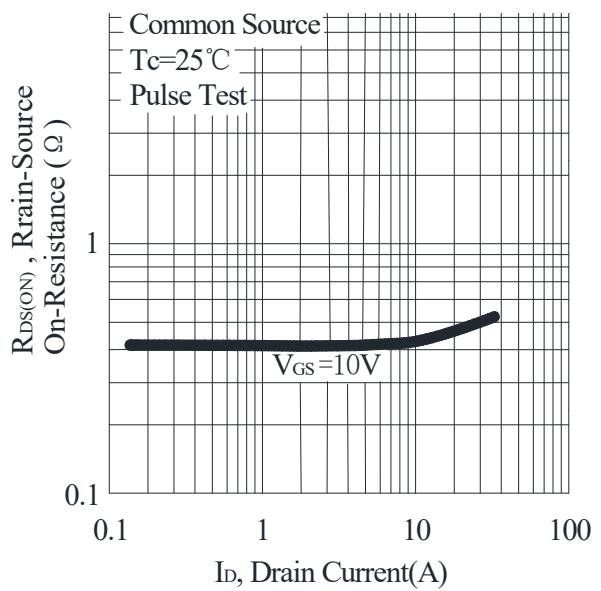
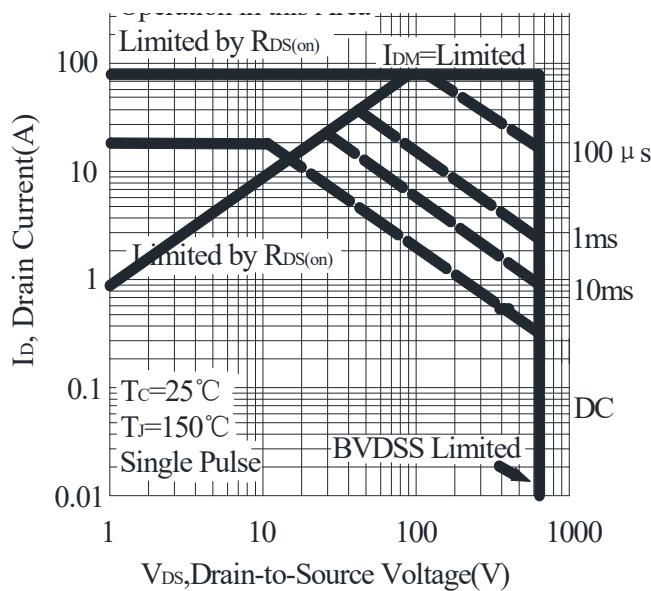
Unclamped Inductive Switching Test Circuit



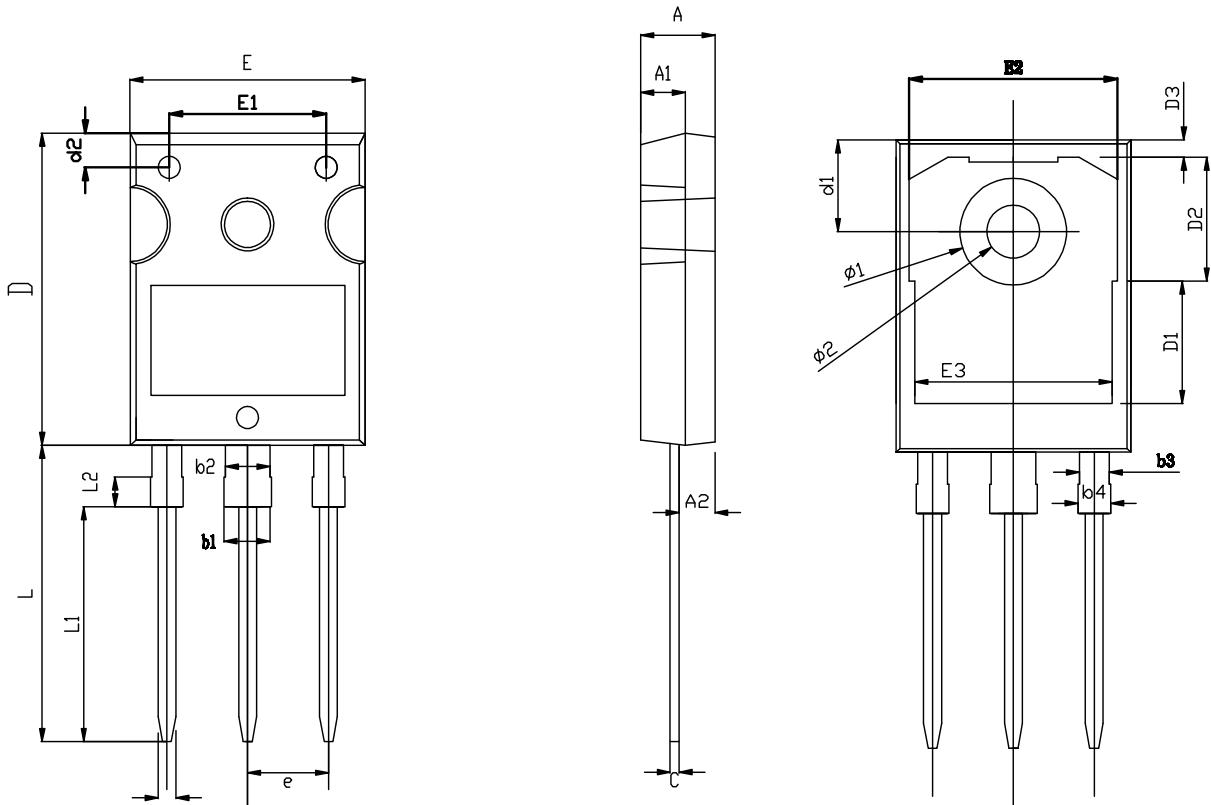
Unclamped Inductive Switching Waveforms

## RATING AND CHARACTERISTIC CURVES

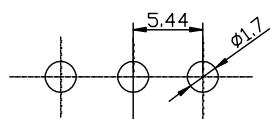




## TO-247-3L PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



UNIT: mm

	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.80	3.00	3.20
A2	2.26	2.41	2.56
b	1.10	1.20	1.30
b1	2.90	-	3.20
b2	2.90	3.00	3.10
b3	1.90	2.00	2.10
b4	2.00	-	2.20
c	0.50	0.60	0.70
D	20.80	21.00	21.20
D1		8.23	
D2		8.32	
D3		1.17	
d1	6.00	6.15	6.30
d2	2.20	2.30	2.40
E	15.60	15.80	16.00
E1		10.50	
E2		14.02	
E3		13.50	
e	5.34	5.44	5.54
L	19.72	19.92	20.12
L1		15.79	
L2		1.98	
ø1	7.10	7.19	7.30
ø2	3.50	3.60	3.70